

Philips

Diode BYX135G

Datasheet

Silicon Diode

BYX135G

5kV/50mA

DATASHEET

OEM – Philips

Source: Philips Databook 1999

High-voltage car ignition diodes**BYX135G****FEATURES**

- Glass passivated
- High maximum operating temperature
- Low leakage current
- Excellent stability
- Guaranteed avalanche energy absorption capability.

DESCRIPTION

Rugged glass package, using a high temperature alloyed construction.

This package is hermetically sealed and fatigue free as coefficients of expansion of all used parts are matched.

The package is designed to be used in an insulating medium such as resin, oil or SF₆ gas.

The BYX135G is marked with a black cathode band on the body.

APPLICATIONS

- Car ignition systems
- Automotive applications with extreme temperature requirements.

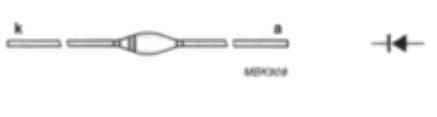


Fig.1 Simplified outline (SOD61ADD) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{RRM}	repetitive peak reverse voltage	*	-	5	kV
V _{RWM}	crest working reverse voltage		-	5	kV
I _{F(AV)}	average forward current		-	50	mA
I _{RSM}	non-repetitive peak reverse current	t = 100 µs triangular pulse; T _j max prior to surge	-	50	mA
T _{stg}	storage temperature		-65	+200	°C
T _j	junction temperature	continuous	-	175	°C
T _j	junction temperature	max. 30 min.	-	200	°C

CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _F	forward voltage	I _F = 10 mA	6.25	8.75	V
V _{(BR)R}	reverse avalanche breakdown voltage	I _R = 100 µA	7.0	9.5	kV
I _R	reverse current	V _R = V _{RWMmax} ; T _j = 175 °C	-	30	µA

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{thJA}	thermal resistance from junction to ambient	T _{amb} = T _{leads} ; lead length = 10 mm	90	K/W